

<b>INFORMATION DISCLOSURE CITATION</b> (Use several sheets if necessary) NOV 03 2003	ATTY DOCKET NO.	SERIAL NO.
	ITO.0552US (P16160)	10/634,140
	APPLICANT(S):	
	TYLER A. LOWREY	
	FILING DATE:	GROUP ART UNIT:
	August 4, 2003	2826

### U.S. PATENT DOCUMENTS

EXAMINER'S INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
A.						
B.						
C.						
D.						

### FOREIGN PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS							
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
E.							
F.							
G.							
H.							

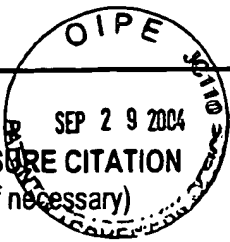
### OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

I.	Hwang, Y.N., Hong, J.S., Lee, S.H., Ahn, S.J., Jeong, G.T., Koh, G.H., Kim, H.J., Jeong, W.C., Lee, S.Y., Park, J.H., Ryoo, K.C., Horii, H., Ha, Y.H., Yi, J.H., Cho, W.Y., Kim, Y.T., Lee, K.H., Joo, S.H., Park, S.O., Jeong, U.I., Jeong, H.S. and Kim, Kinam, "Completely CMOS-Compatible Phase-Change Nonvolatile RAM Using NMOS Cell Transistors," presented at 2003 19 <sup>th</sup> IEEE Non-Volatile Semiconductor Memory Workshop, Monterey, California, February 26-20, 2003
J.	Ha, Y.H., Yi, J.H., Horii, H., Park, J.H., Joo, S.H., Park, S.O., Chung, U-In and Moon, J.T., "An Edge Contact Type Cell for Phase Change RAM Featuring Very Low Power Consumption," presented at IEEE 2003 Symposium on VLSI Technology, Kyoto, Japan, June 12-14, 2003
K.	Hwang, Y.N., Hong, J.S., Lee, S.H., Ahn, S.J., Jeong, G.T., Koh, G.H., Oh, J.H., Kim, H.J., Jeong, W.C., Lee, S.Y., Park, J.H., Ryoo, K.C., Horii, H., Ha, Y.H., Yi, J.H., Cho, W.Y., Kim, Y.T., Lee, K.H., Joo, S.H., Park, S.O., Chung, U.I., Jeong, H.S. and Kim, Kinam, "Full Integration and Reliability Evaluation of Phase-change RAM Based on 0.24 mm-CMOS Technologies," presented at IEEE 2003 Symposium on VLSI Technology, Kyoto, Japan, June 12-14, 2003
L.	Horii, H., Yi, J.H., Park, J.H., Ha, Y.H., Baek, I.G., Park, S.O., Hwang, Y.N., Lee, S.H., Kim, Y.T., Lee, K.H., Chung, U-In and Moon, J.T., "A Novel Cell Technology Using N-doped GeSbTe Films for Phase Change RAM," presented at IEEE 2003 Symposium on VLSI Technology, Kyoto, Japan, June 12-14, 2003
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EXAMINER

DATE CONSIDERED

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ATTY DOCKET NO.  
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APPLICANT(S):  
Tyler A. Lowrey

FILING DATE:  
August 4, 2004

GROUP ART UNIT:  
2826

**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
g.f.	A.	6,579,760	06/17/2003	Lung	438	257	—
	B.						
	C.						
	D.						
	E.						

**U.S. PATENT APPLICATION PUBLICATIONS**

g.f.	F.	2003/0001230	01/02/2003	Lowrey	257	529	—
	G.						
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**FOREIGN PATENT DOCUMENTS**

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
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g.f.	M.	WO 2004/055828	07/01/2004	PCT				
g.f.	N.	WO 2004/055899	07/01/2004	PCT				
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<del>Q.</del>	
<del>R.</del>	
<del>S.</del>	
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<del>U.</del>	
<del>V.</del>	

EXAMINER

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03/02/05

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